

19.[Amended]

A device produced according to the method of [claim 1] making a silicon micromechanical structure, comprising the steps of:  
forming a lightly doped silicon substrate having a first and second side and having less than  $5 \times 10^{19} \text{ cm}^{-3}$  boron therein;  
placing a p+ layer on the first side of said substrate, said p+ having a boron content of greater than  $7 \times 10^{19} \text{ cm}^{-3}$  and a germanium content of about  $1 \times 10^{21} \text{ cm}^{-3}$ ;  
forming a mask on the second side for etching a predetermined pattern;  
etching said second side to said p+ layer; and  
depositing an insulator on said p+ layer and fabricating an electronic component on said insulator.

28.[Amended]

A device produced according to the method of [claim 10.] making a silicon micromechanical structure, comprising the steps of:  
forming a lightly doped silicon substrate having a first and second side and having less than  $5 \times 10^{19} \text{ cm}^{-3}$  boron therein;  
placing a p+ layer on the first side of said substrate, said p+ having a boron content of greater than  $7 \times 10^{19} \text{ cm}^{-3}$  and a germanium content of about  $1 \times 10^{21} \text{ cm}^{-3}$ ;  
forming a lightly doped layer on said p+ layer to form a buried p+ layer;  
forming a mask on the second side for etching a predetermined pattern;  
etching said second side to said buried p+ layer; and  
depositing an insulator on said lightly doped layer and fabricating an electronic component on said insulator.